# NEC

### PNP SILICON DARLINGTON TRANSISTOR

## 2SB1149

**DESCRIPTION** The 2SB1149 is a darlington transistor built-in dumper diode

at E-C.

It is suitable for use to operate from IC without predfiver, such as hammer driver.

**FEATURES** 

- High DC Current Gain.
- Low Collector Saturation Voltage.
- Built-in a dumper diode at E-C.
- High Power Dissipation:  $P_T = 1.3 \text{ W} \text{ (at } T_a = 25 ^{\circ}\text{C)}$

#### **ABSOLUTE MAXIMUM RATINGS**

Maximum Temperatures

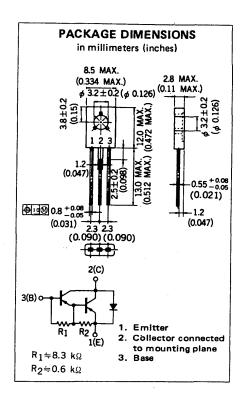
**Maximum Power Dissipations** 

Total Power Dissipation ( $T_a = 25 \,^{\circ}C$ ) . . . . . 1.3 W Total Power Dissipation ( $T_c = 25 \,^{\circ}C$ ) . . . . . 15 W

Maximum Voltages and Currents (T<sub>a</sub> = 25 °C)

V CBO	Collector to base voltage – roo	V
V <sub>CEO</sub>	Collector to Emitter Voltage $-100$	٧
$V_{EBO}$	Emitter to Base Voltage $-8.0$	٧
I <sub>C(DC)</sub>	Collector Current ∓3.0	Α
C(pulse) *	Collector Current	Α

\* PW  $\leq$  10 ms, Duty Cycle  $\leq$  50 %



#### ELECTRICAL CHARACTERISTICS ( $T_a = 25$ °C)

SYMBOL	CHARACTERISTIC	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
hFE1**	DC Current Gain	2000		15000	_	V <sub>CE</sub> = -2.0 V, I <sub>C</sub> = -1.5 A
hFE2**	DC Current Gain	1000				$V_{CE} = -2.0 \text{ V, } I_{C} = -3.0 \text{ A}$
ton	Turn On Time		0.5		μs	$I_{\rm C} = -1.5  A,  R_{\rm L} = 27  \Omega$
<sup>t</sup> stg	Storage Time		2.0		μs	$I_{C} = -1.5 \text{ A}, R_{L} = 27 \Omega$ $I_{B1} = -I_{B2} = -1.5 \text{ mA}, V_{CC} = -40 \text{ V}$
t <sub>f</sub>	Fall Time		1.0		μs	See Test Circuit.
ІСВО	Collector Cutoff Current			-10	μΑ	$V_{CB} = -100 \text{ V, I}_{E} = 0$
I <sub>EBO</sub>	Emitter Cutoff Current			-1.0	mA	$V_{EB} = -5.0 \text{ V, } I_{C} = 0$
V <sub>CE(sat)</sub> **	Collector Saturation Voltage		-0.9	-1.2	V	$I_C = -1.5 \text{ A}, I_B = -1.5 \text{ mA}$
VBE(sat)**	Base Saturation Voltage		-1.5	-2.0	V	$I_C = -1.5 \text{ A}, I_B = -1.5 \text{ mA}$

<sup>\*\*</sup> Pulsed / PW  $\leqq$  350  $\mu \text{s}$  , Duty Cycle  $\leqq$  2 %

#### Classification of hee1

Rank	М	L	K ·							
Range	2000 to 5000	3000 to 7000	5000 to 15000							

Test Conditions: V<sub>CE</sub> = -2.0 V, I<sub>C</sub> = -1.5 A

#### TYPICAL CHARACTERISTICS (Ta = 25 °C)

